

Hiroshi Oka

List of Publications by Year in descending order

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Version: 2024-02-01

20
papers

110
citations

1478505

6
h-index

1372567

10
g-index

20
all docs

20
docs citations

20
times ranked

135
citing authors

#	ARTICLE	IF	CITATIONS
1	Comprehensive study and design of scaled metal/high-k/Ge gate stacks with ultrathin aluminum oxide interlayers. Applied Physics Letters, 2015, 106, 233503.	3.3	20
2	Fabrication of tensile-strained single-crystalline GeSn on transparent substrate by nucleation-controlled liquid-phase crystallization. Applied Physics Letters, 2017, 110, .	3.3	16
3	Comparative study of GeO ₂ /Ge and SiO ₂ /Si structures on anomalous charging of oxide films upon water adsorption revealed by ambient-pressure X-ray photoelectron spectroscopy. Journal of Applied Physics, 2016, 120, .	2.5	11
4	Verification of influence of tail states and interface states on sub-threshold swing of Si n-channel MOSFETs over a temperature range of 4â€“300 K. Japanese Journal of Applied Physics, 2022, 61, SC1032.	1.5	11
5	Back-side illuminated GeSn photodiode array on quartz substrate fabricated by laser-induced liquid-phase crystallization for monolithically-integrated NIR imager chip. , 2017, , .		7
6	Phosphorous ion implantation into NiGe layer for Ohmic contact formation on n-type Ge. Japanese Journal of Applied Physics, 2014, 53, 08LD01.	1.5	6
7	Schottky source/drain germanium-based metal-oxide-semiconductor field-effect transistors with self-aligned NiGe/Ge junction and aggressively scaled high- <i>k</i> gate stack. Applied Physics Letters, 2015, 107, .	3.3	6
8	Lightly doped n-type tensile-strained single-crystalline GeSn-on-insulator structures formed by lateral liquid-phase crystallization. Applied Physics Express, 2018, 11, 011304.	2.4	6
9	Understanding and engineering of NiGe/Ge junction formed by phosphorous ion implantation after germanidation. Applied Physics Letters, 2014, 105, 062107.	3.3	5
10	High-mobility TFT and enhanced luminescence utilizing nucleation-controlled GeSn growth on transparent substrate for monolithic optoelectronic integration. , 2016, , .		5
11	Ultra-thin germanium-tin on insulator structure through direct bonding technique. Semiconductor Science and Technology, 2018, 33, 124002.	2.0	5
12	Non-equilibrium solid-phase growth of amorphous GeSn layer on Ge-on-insulator wafer induced by flash lamp annealing. Applied Physics Express, 2021, 14, 025505.	2.4	3
13	Flash lamp annealing processing to improve the performance of high-Sn content GeSn n-MOSFETs. Applied Physics Express, 2021, 14, 096501.	2.4	3
14	Effect of percolation path on temperature dependence of threshold voltage variability in bulk MOSFETs. Japanese Journal of Applied Physics, 0, , .	1.5	2
15	Importance of source and drain extension design in cryogenic MOSFET operation: causes of unexpected threshold voltage increases. Applied Physics Express, 2022, 15, 084004.	2.4	2
16	Schottky barrier height reduction of NiGe/Ge junction by P ion implantation for metal source/drain Ge CMOS devices. , 2014, , .		1
17	High-mobility GeSn p-MOSFETs on transparent substrate utilizing nucleation-controlled liquid-phase crystallization. , 2016, , .		1
18	Sub-1-nm EOT Schottky source/drain Germanium CMOS technology with low-temperature self-aligned NiGe/Ge junctions. , 2014, , .		0

#	ARTICLE	IF	CITATIONS
19	Schottky barrier height modulation at NiGe/Ge interface by phosphorous ion implantation and its application to Ge-based CMOS devices. , 2015, , .		0
20	Effect of Random Potential Fluctuations on Threshold Voltage Variability in Bulk MOSFETs at Cryogenic Temperature. , 2022, , .		0